

WHAT IS CLAIMED IS:

1. A method of making a semiconductor device comprising:
 - providing a wafer on which are formed electrodes;
 - providing a stress relieving layer on the wafer in such a way as to avoid at least a part of the electrodes, the stress relieving layer formed to have a sloping edge;
 - forming wiring over the stress relieving layer from the electrodes, a width of the wiring being greater than a width of each of the electrodes at a junction of the wiring and each of the electrodes, the wiring formed to have a narrower portion on the sloping edge than one of the electrodes;
 - forming the external electrodes connected to the wiring above the stress relieving layer; and
 - cutting the wafer into individual pieces.
2. A method of making an electronic component comprising:
 - integrally forming a plurality of electronic elements in a substrate form, each of the electronic elements having electrodes;
 - providing a stress relieving layer at least in regions where are formed external electrodes of the electronic elements in the substrate form, the stress relieving layer formed to have a sloping edge;
 - forming wiring over the stress relieving layer from the electrodes, a width of the wiring being greater than a width of each of the electrodes at a junction of the wiring and each of the electrodes, the wiring formed to have a narrower portion on the sloping edge than one of the electrodes;
 - forming the external electrodes on the stress relieving layer; and
 - cutting the electronic elements in the substrate form into individual pieces.